

a first layer of conductive material formed on the surface of the glass sheet, wherein the conductive material is formed to create metallized pads adjacent to the holes in the glass sheet;

a layer of adhesive material disposed on the surface of the semiconductor wafer, wherein the layer of adhesive material affixes the glass sheet to the semiconductor wafer such that the holes in the glass sheet are aligned with the location of the bond pads on the semiconductor wafer;

a second layer of conductive material formed on the surface of the glass sheet, wherein the second layer of conductive material extends through the holes in the glass sheet to electrically connect the metallized pads on the glass sheet to the bond pads on the surface of the semiconductor wafer; and

a plurality of solder balls disposed on the metallized pads such that an electrical connection is made between the solder ball and the conductive material.

19. The semiconductor package of Claim 18, and wherein the semiconductor wafer contains a plurality of semiconductor die and the semiconductor wafer is disposed to be divided into a plurality of individual packaged semiconductor die.

20. The semiconductor package of Claim 18 or 19, wherein the glass sheet has a coefficient of thermal expansion that is substantially the same as the coefficient of thermal expansion of the semiconductor wafer.

21. The semiconductor package of Claim 18 or 19, wherein the semiconductor wafer is silicon

22. The semiconductor package of Claim 18 or 19, wherein the first conductive layer is a metal selected from the group consisting of aluminum, nickel, gold, or copper.

23. The semiconductor package of Claim 18 or 19, wherein the second conductive layer is a metal selected from the group consisting of aluminum or gold.

24. The semiconductor package of Claim 18 or 19, wherein the second conductive layer is a conductive polymer.

25. A semiconductor package comprising:

a semiconductor wafer having at least one semiconductor die created therein;

a plurality of bond pads formed on a surface of the semiconductor wafer;

a glass sheet having a first surface and a second surface and having holes formed therein, wherein the size of the glass sheet matches the size of the semiconductor wafer;

a first layer of conductive material formed on the first surface of the glass sheet, wherein the conductive material is formed to create metallized pads adjacent to the holes in the glass sheet;

a layer of adhesive material disposed on the surface of the semiconductor wafer, wherein the layer of adhesive material affixes the glass sheet to the semiconductor wafer such that the holes in the glass sheet are aligned with the location of the bond pads on the semiconductor wafer and the second surface of the glass sheet is in direct contact with the adhesive material;

of the glass sheet, wherein the second layer of conductive material

extends through the holes in the glass sheet to electrically connect the metallized pads on the glass sheet to the bond pads on the surface of the semiconductor wafer; and

a plurality of solder balls on the metallized pads such that an electrical connection is made between the solder ball and the metallized pad.

26. The semiconductor package of Claim 25, and wherein the semiconductor wafer contains a plurality of semiconductor die and the semiconductor wafer is disposed to be divided into a plurality of individual packaged semiconductor die.

27. The semiconductor package of Claim 25 or 26, wherein the glass sheet has a coefficient of thermal expansion that is substantially the same as the coefficient of thermal expansion of the semiconductor wafer.

28. The semiconductor package of Claim 25 or 26, wherein the semiconductor wafer is silicon.

29. The semiconductor package of Claim 25 or 26, wherein the first conductive layer is a metal selected from the group consisting of aluminum, nickel, gold, or copper.

30. The semiconductor package of Claim 25 or 26, wherein the second conductive layer is a metal selected from the group consisting of aluminum or gold.

31. The semiconductor package of Claim 25 or 26, wherein the second conductive layer is a conductive polymer.

32. A semiconductor package comprising:

created therein.

a plurality of bond pads formed on a surface of the semiconductor wafer;

a glass sheet having holes formed therein, wherein the size of the glass sheet matches the size of the semiconductor wafer;

a first layer of conductive material formed on the surface of the glass sheet, wherein the conductive material is formed to create metallized pads adjacent to the holes in the glass sheet;

a layer of adhesive material disposed on the surface of the semiconductor wafer, wherein the layer of adhesive material affixes the glass sheet to the semiconductor wafer such that the holes in the glass sheet are aligned with the location of the bond pads on the semiconductor wafer;

a second layer of conductive material formed on the surface of the glass sheet, wherein the conductive material extends through the holes in the glass sheet to electrically connect the metallized pads on the glass sheet to the bond pads on the surface of the semiconductor wafer;

a non-conductive mask deposited on the surface of the glass sheet, wherein the non-conductive mask covers the first and second conductive layers and is etched to create holes above the metallized pads,

a plurality of solder balls disposed on the metallized pads such that an electrical connection is made between the solder ball and the conductive material.

33. The semiconductor package of Claim 32, and wherein the

individual packaged semiconductor die